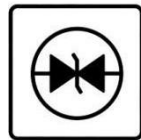


# MSKSEMI 美森科

SEMICONDUCTOR



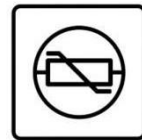
ESD



TVS



TSS



MOV



GDT



PLED

## BAT54/A/C/S LT1G-MS

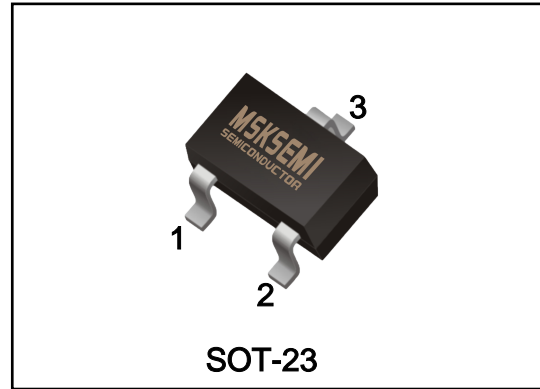
Product specification

SCHOTTKY DIODES

FEATURES

- Extremely Fast Switching Speed

PACKAGE OUTLINE



PINCONFIGURATIONANDMARKING

BAT54LT1G-MS	MARKING
	<b>JV3*</b>

BAT54ALT1G-MS	MARKING
	<b>B6 *</b>

BAT54CLT1G-MS	MARKING
	<b>5C *</b>

BAT54SLT1G-MS	MARKING
	<b>LD3*</b>

**Maximum Ratings @TA=25°C**

Parameter	Symbol	Limits	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	30	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
Forward Continuous Current	$I_{FM}$	200	mA
Power Dissipation	$P_D$	200	mW
Storage temperature	$T_{STG}$	-55-150	°C

**Electrical Characteristics @TA=25°C**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	30			V	$I_R=100\mu A$
Forward voltage	$V_{F1}$			0.24	V	$I_F=0.1mA$
	$V_{F2}$			0.32	V	$I_F=1mA$
	$V_{F3}$			0.40	V	$I_F=10mA$
	$V_{F4}$			0.50	V	$I_F=30mA$
	$V_{F5}$			1	V	$I_F=100mA$
Reverse current	$I_R$			2	$\mu A$	$V_R=25V$
Diode Capacitance	$C_D$			15	pF	$V_R=1V, f=1MHz$
Reverse Recovery Time	$t_{rr}$			5	nS	$I_F=I_R=10mA$ $I_{rr}=0.1I_R, R_L=100\Omega$

Typical Characteristics

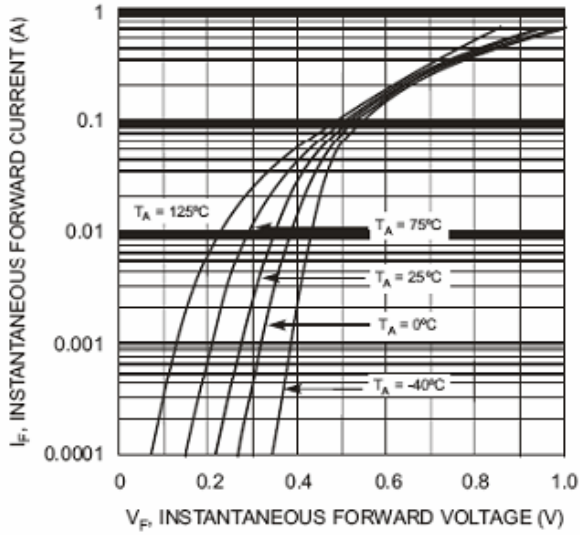


Fig. 1 Forward Characteristics

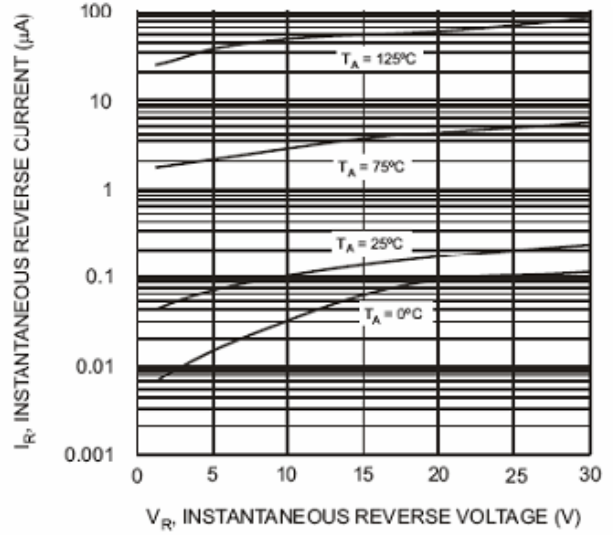


Fig. 2 Typical Reverse Characteristics

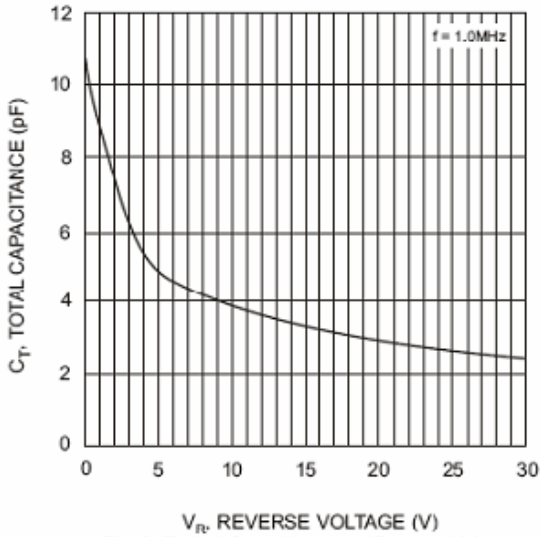


Fig. 3 Typical Capacitance vs. Reverse Voltage

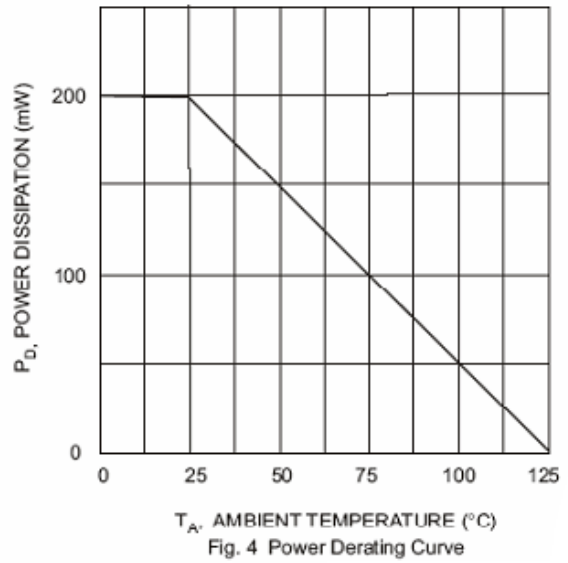
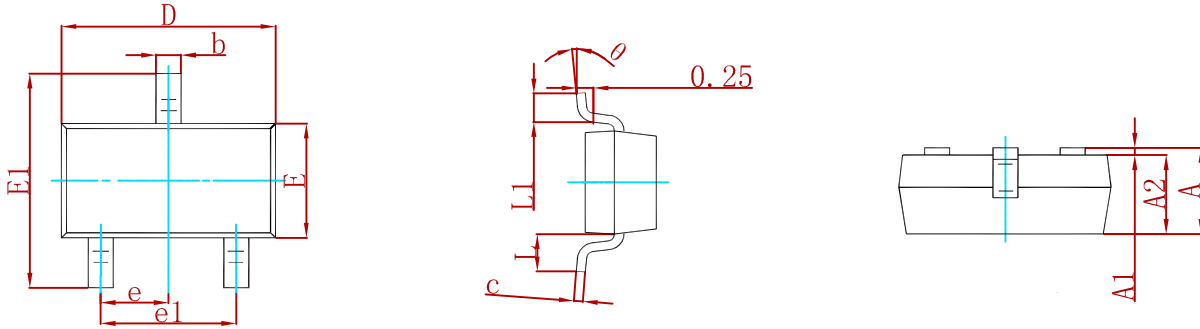


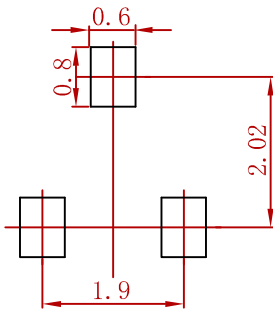
Fig. 4 Power Derating Curve

**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ± 0.05mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
BAT54/A/C/S LT1G-MS	SOT-23	3000

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